Elektronische Bauelemente

2N4126

-0.2 A, -25 V

PNP Plastic Encapsulated Transistor

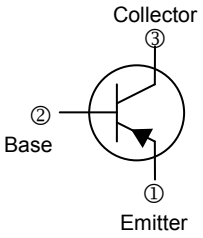
RoHS Compliant Product

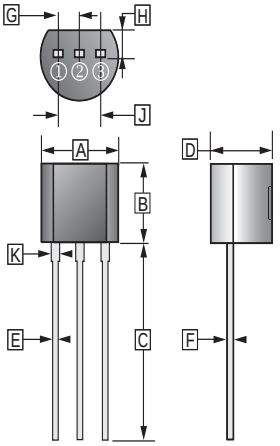
A suffix of "-C" specifies halogen & lead-free

FEATURES

TO-92

- PNP Silicon Epitaxial Transistor for Switching and Amplifier Applications.
- Complementary of the 2N4124





① Emitter
② Base
③ Collector

REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-25	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-4	V
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	625	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	200	°C / W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-25	-	-	V	I_C= -0.01mA, I_E = 0A
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25	-	-	V	I_C=-1mA, I_B = 0A
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-4	-	-	V	I_E= -0.01mA, I_C = 0A
Collector Cut-Off Current	I_{CBO}	-	-	-50	nA	V_{CB}=- 20V, I_E = 0 A
Emitter Cut-Off Current	I_{EBO}	-	-	-50	nA	V_{EB}= -3V, I_C = 0 mA
DC Current Gain	$h_{FE\ (1)}$*	120	-	360		V_{CE}= -1V, I_C= -2 mA
	$h_{FE\ (2)}$*	60	-	-		V_{CE}= -1V, I_C=-50mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$*	-	-	-0.4	V	I_C=-50mA, I_B=-5mA
Base to Emitter Saturation Voltage	$V_{BE(sat)}$*	-	-	-0.95	V	I_C=-50mA, I_B=-5mA
Collector output Capacitance	C_{ob}	-	-	4.5	pF	V_{CB} = -5V, I_E = 0A, f=1MHz
Transition Frequency	f_T	250	-	-	MHz	V_{CE} = -20V, I_C = -10mA, f=100MHz

*Pulse test : pulse width ≦ 300μs, duty cycle ≦ 1.5%.